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March 2014

## FQP12N60C

### N-Channel QFET® MOSFET

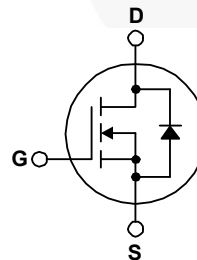
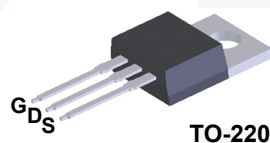
600 V, 12 A, 650 mΩ

#### Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies, active power factor correction, electronic lamp ballast based on half bridge topology.

#### Features

- 12 A, 600 V,  $R_{DS(on)} = 650 \text{ m}\Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 6 \text{ A}$
- Low Gate Charge (Typ. 48 nC)
- Low  $C_{rss}$  (Typ. 21 pF)
- 100% Avalanche Tested



#### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol         | Parameter                                                                                                | FQP12N60C   | Unit                     |
|----------------|----------------------------------------------------------------------------------------------------------|-------------|--------------------------|
| $V_{DSS}$      | Drain-Source Voltage                                                                                     | 600         | V                        |
| $I_D$          | Drain Current<br>- Continuous ( $T_C = 25^\circ\text{C}$ )<br>- Continuous ( $T_C = 100^\circ\text{C}$ ) | 12<br>7.4   | A<br>A                   |
| $I_{DM}$       | Drain Current - Pulsed (Note 1)                                                                          | 48          | A                        |
| $V_{GSS}$      | Gate-Source voltage                                                                                      | $\pm 30$    | V                        |
| $E_{AS}$       | Single Pulsed Avalanche Energy (Note 2)                                                                  | 870         | mJ                       |
| $I_{AR}$       | Avalanche Current (Note 1)                                                                               | 12          | A                        |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)                                                                     | 22.5        | mJ                       |
| $dv/dt$        | Peak Diode Recovery $dv/dt$ (Note 3)                                                                     | 4.5         | V/ns                     |
| $P_D$          | Power Dissipation ( $T_C = 25^\circ\text{C}$ )<br>- Derate above $25^\circ\text{C}$                      | 225<br>1.78 | W<br>W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                                                                  | -55 to +150 | $^\circ\text{C}$         |
| $T_L$          | Maximum Lead Temperature for Soldering Purpose,<br>1/8" from Case for 5 Seconds                          | 300         | $^\circ\text{C}$         |

\*Drain current limited by maximum junction temperature

#### Thermal Characteristics

| Symbol          | Parameter                                     | FQP12N60C | Unit                      |
|-----------------|-----------------------------------------------|-----------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max.    | 0.56      | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 62.5      | $^\circ\text{C}/\text{W}$ |

## Package Marking and Ordering Information

| Part Number | Top Mark  | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|-----------|---------|----------------|-----------|------------|----------|
| FQP12N60C   | FQP12N60C | TO-220  | Tube           | N/A       | N/A        | 50 units |

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted.

| Symbol                                                 | Parameter                                             | Conditions                                                                                       | Min      | Typ      | Max     | Unit     |
|--------------------------------------------------------|-------------------------------------------------------|--------------------------------------------------------------------------------------------------|----------|----------|---------|----------|
| Off Characteristics                                    |                                                       |                                                                                                  |          |          |         |          |
| BV <sub>DSS</sub>                                      | Drain-Source Breakdown Voltage                        | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA, T <sub>J</sub> = 25°C                            | 600      | --       | --      | V        |
| ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>                   | Breakdown Voltage Temperature Coefficient             | I <sub>D</sub> = 250 μA, Referenced to 25°C                                                      | --       | 0.5      | --      | V/°C     |
| I <sub>DSS</sub>                                       | Zero Gate Voltage Drain Current                       | V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V<br>V <sub>DS</sub> = 480 V, T <sub>C</sub> = 125° | --<br>-- | --<br>-- | 1<br>10 | μA<br>μA |
| I <sub>GSSF</sub>                                      | Gate-Body Leakage Current, Forward                    | V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V                                                    | --       | --       | 100     | nA       |
| I <sub>GSSR</sub>                                      | Gate-Body Leakage Current, Reverse                    | V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V                                                   | --       | --       | -100    | nA       |
| On Characteristics                                     |                                                       |                                                                                                  |          |          |         |          |
| V <sub>GS(th)</sub>                                    | Gate Threshold Voltage                                | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                      | 2.0      | --       | 4.0     | V        |
| R <sub>DS(on)</sub>                                    | Static Drain-Source On-Resistance                     | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6 A                                                     | --       | 0.53     | 0.65    | Ω        |
| g <sub>FS</sub>                                        | Forward Transconductance                              | V <sub>DS</sub> = 40 V, I <sub>D</sub> = 6 A                                                     | --       | 13       | --      | S        |
| Dynamic Characteristics                                |                                                       |                                                                                                  |          |          |         |          |
| C <sub>iss</sub>                                       | Input Capacitance                                     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,<br>f = 1.0 MHz                                    | --       | 1760     | 2290    | pF       |
| C <sub>oss</sub>                                       | Output Capacitance                                    |                                                                                                  | --       | 182      | 235     | pF       |
| C <sub>rss</sub>                                       | Reverse Transfer Capacitance                          |                                                                                                  | --       | 21       | 28      | pF       |
| Switching Characteristics                              |                                                       |                                                                                                  |          |          |         |          |
| t <sub>d(on)</sub>                                     | Turn-On Delay Time                                    | V <sub>DD</sub> = 300 V, I <sub>D</sub> = 12 A<br>R <sub>G</sub> = 25 Ω<br><br>(Note 4)          | --       | 30       | 70      | ns       |
| t <sub>r</sub>                                         | Turn-On Rise Time                                     |                                                                                                  | --       | 85       | 180     | ns       |
| t <sub>d(off)</sub>                                    | Turn-Off Delay Time                                   |                                                                                                  | --       | 140      | 280     | ns       |
| t <sub>f</sub>                                         | Turn-Off Fall Time                                    |                                                                                                  | --       | 90       | 190     | ns       |
| Q <sub>g</sub>                                         | Total Gate Charge                                     | V <sub>DS</sub> = 400 V, I <sub>D</sub> = 12 A<br>V <sub>GS</sub> = 10 V<br><br>(Note 4)         | --       | 48       | 63      | nC       |
| Q <sub>gs</sub>                                        | Gate-Source Charge                                    |                                                                                                  | --       | 8.5      | --      | nC       |
| Q <sub>gd</sub>                                        | Gate-Drain Charge                                     |                                                                                                  | --       | 21       | --      | nC       |
| Drain-Source Diode Characteristics and Maximum Ratings |                                                       |                                                                                                  |          |          |         |          |
| I <sub>S</sub>                                         | Maximum Continuous Drain-Source Diode Forward Current |                                                                                                  | --       | --       | 12      | A        |
| I <sub>SM</sub>                                        | Maximum Pulsed Drain-Source Diode Forward Current     |                                                                                                  | --       | --       | 48      | A        |
| V <sub>SD</sub>                                        | Drain-Source Diode Forward Voltage                    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 12 A                                                      | --       | --       | 1.4     | V        |
| t <sub>rr</sub>                                        | Reverse Recovery Time                                 | V <sub>GS</sub> = 0V, I <sub>S</sub> = 12 A                                                      | --       | 420      | --      | ns       |
| Q <sub>rr</sub>                                        | Reverse Recovery Charge                               | dI <sub>F</sub> /dt = 100 A/μs                                                                   | --       | 4.9      | --      | μC       |

### NOTES:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. L = 11 mH, I<sub>AS</sub> = 12 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.
3. I<sub>SD</sub> ≤ 12 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C.
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

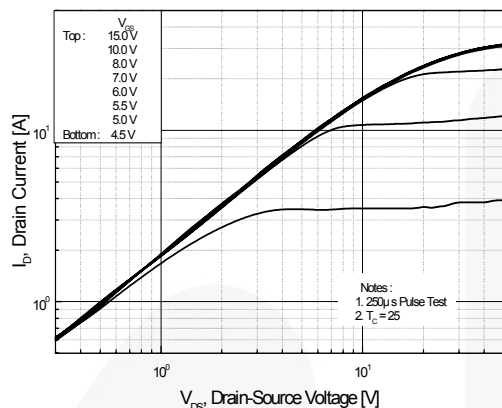


Figure 2. Transfer Characteristics

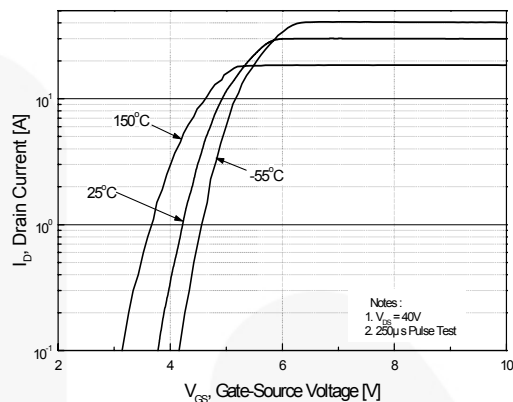


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

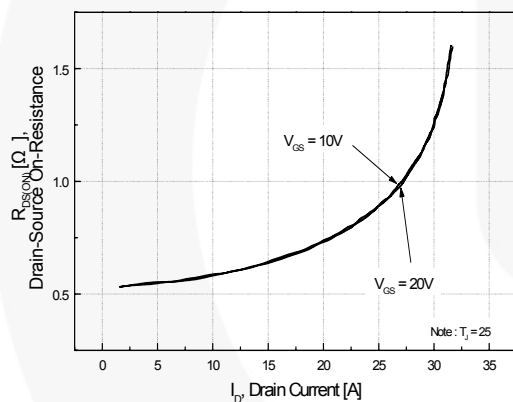


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

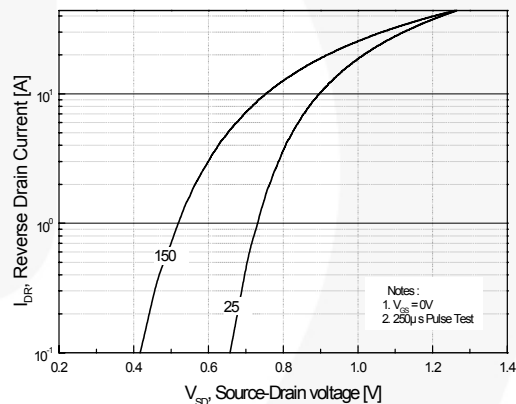


Figure 5. Capacitance Characteristics

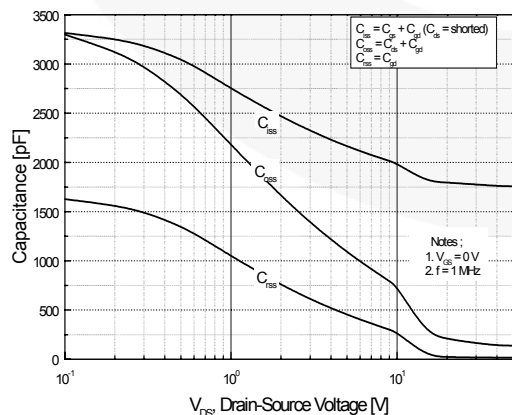
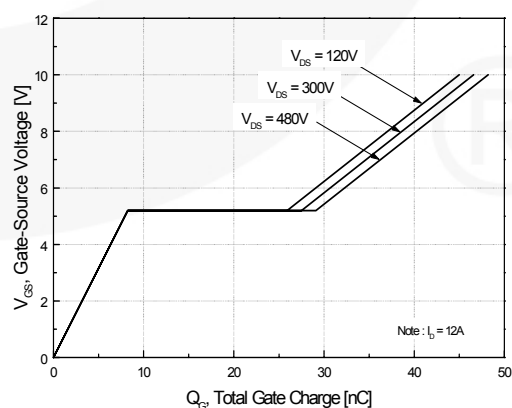


Figure 6. Gate Charge Characteristics



## Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

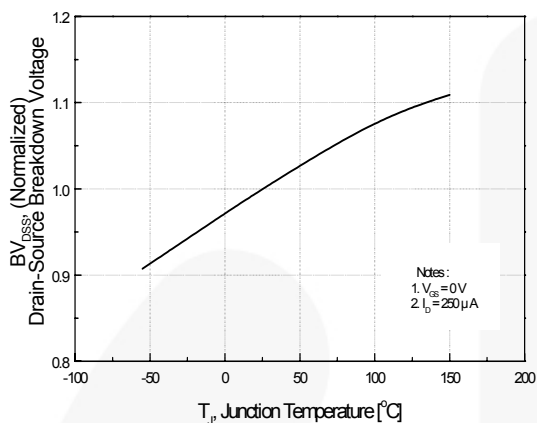


Figure 8. On-Resistance Variation vs. Temperature

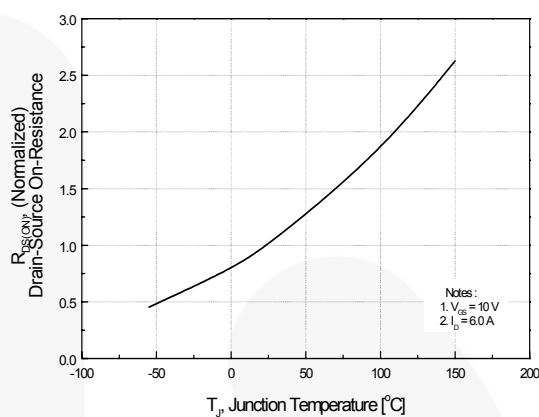


Figure 9. Maximum Safe Operating Area

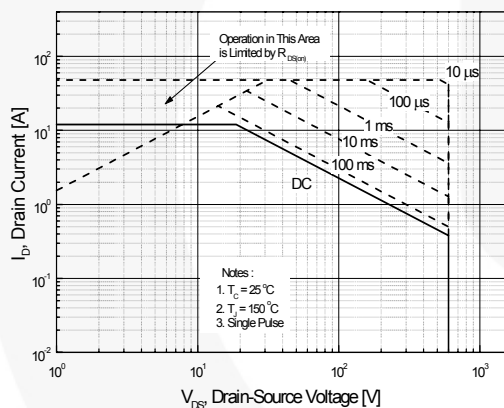


Figure 10. Maximum Drain Current vs. Case Temperature

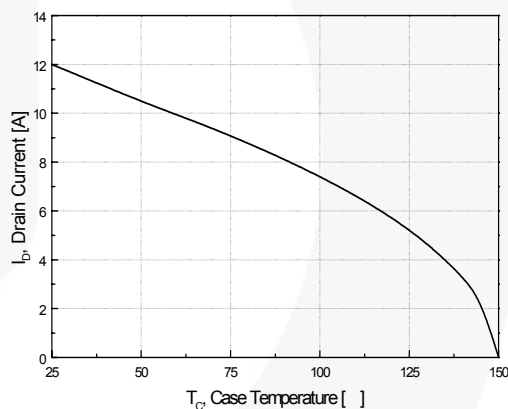
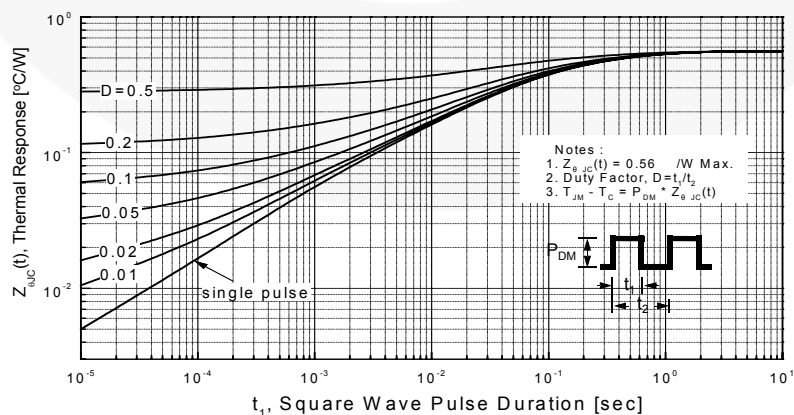


Figure 11. Transient Thermal Response Curve



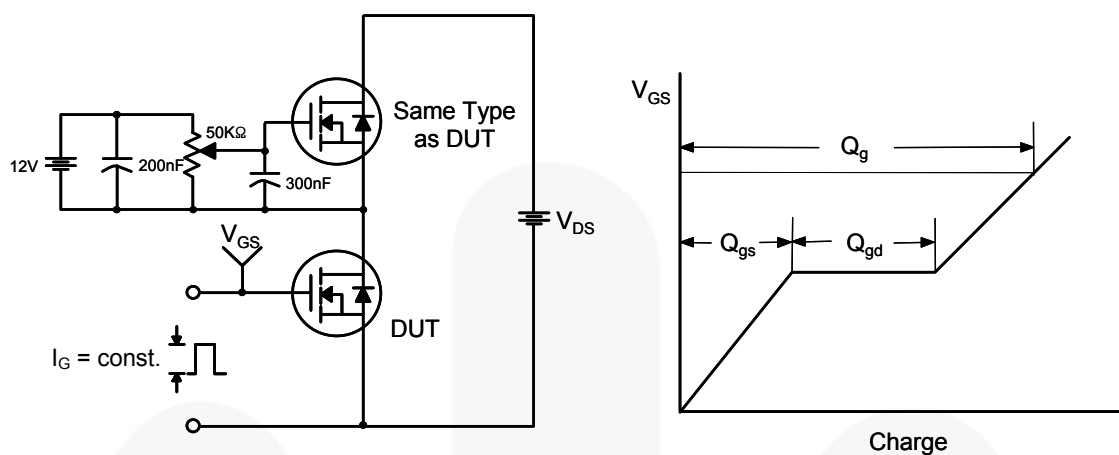


Figure 12. Gate Charge Test Circuit & Waveform

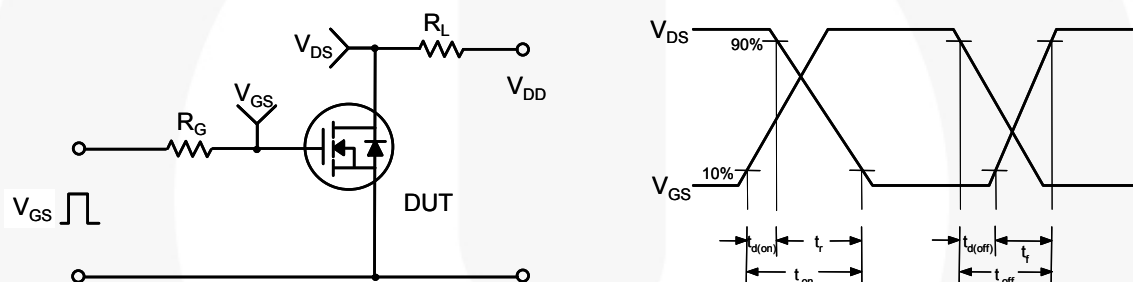


Figure 13. Resistive Switching Test Circuit & Waveforms

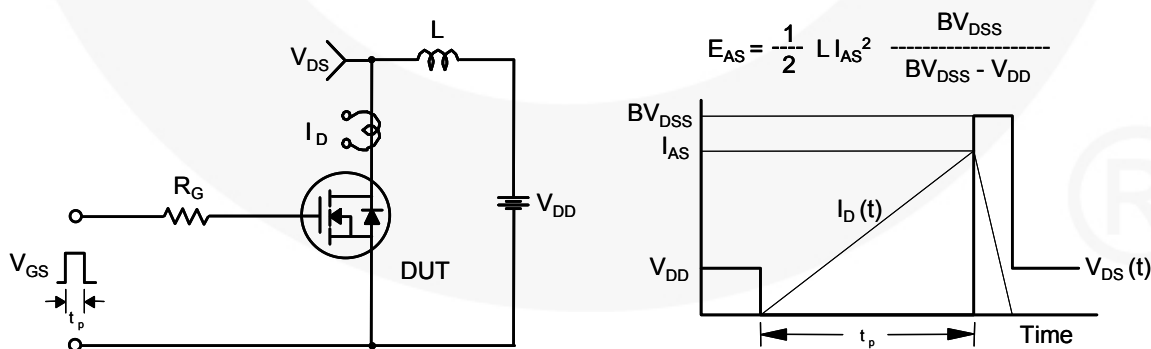


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

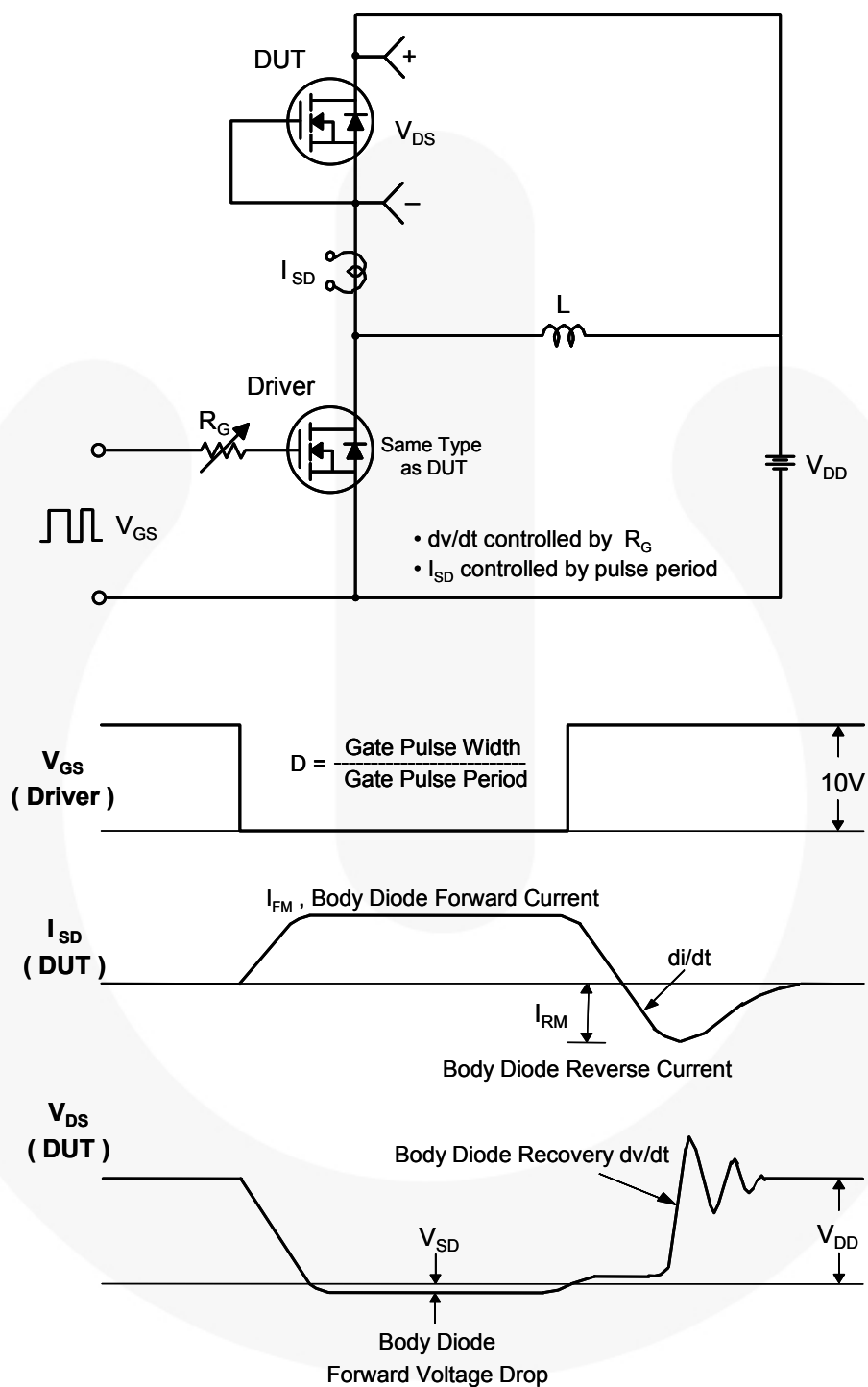
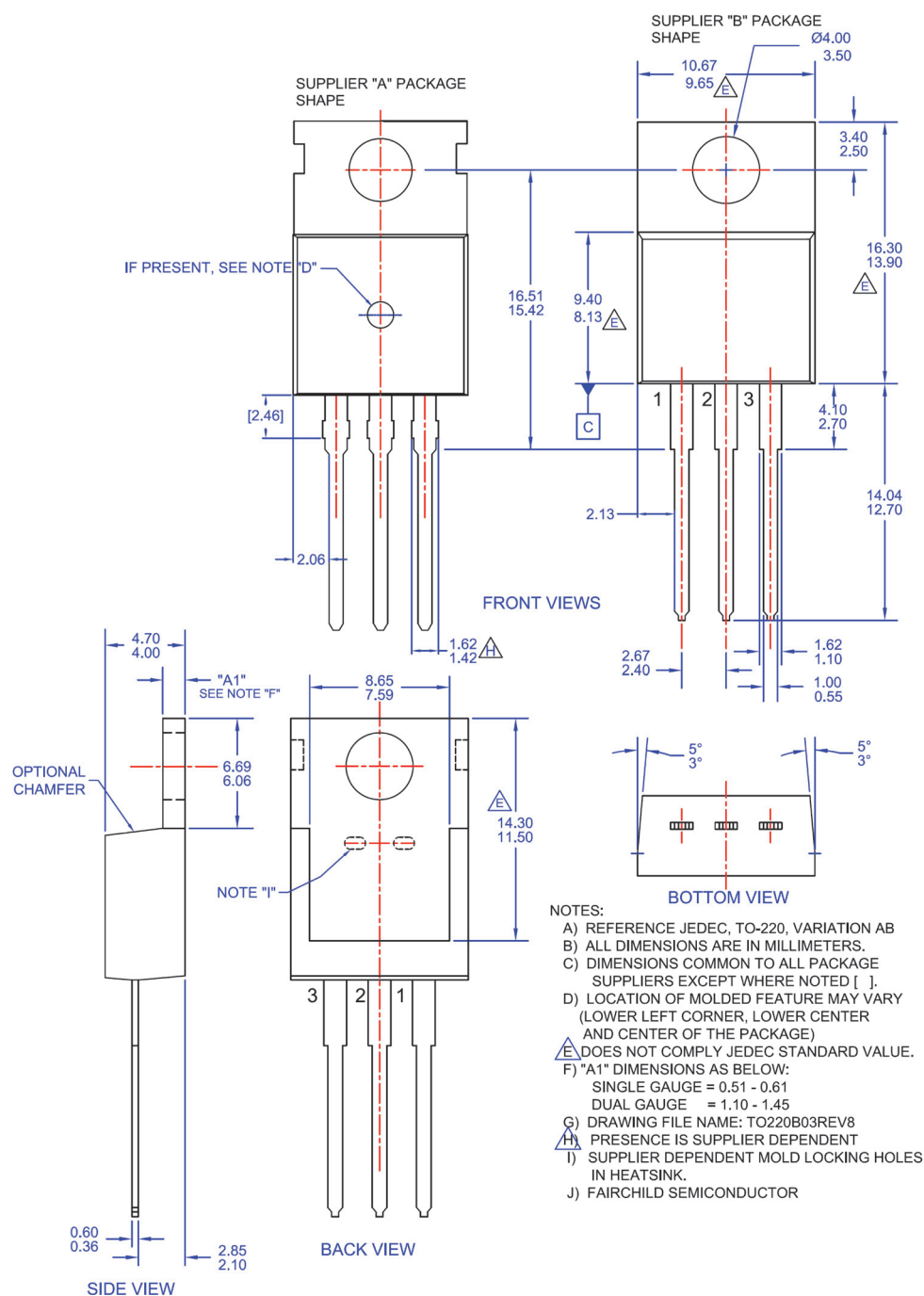


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

# Mechanical Dimensions



**Figure 16. TO220, Molded, 3-Lead, Non Jedec Variation AB**

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- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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